10/632 155

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	408	(nonvolatile adj memory adj cell) and source and drain and channel and region and n-type and p-type and floating and gate and concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 13:35
L2	122	(nonvolatile adj memory adj cell) and source and drain and channel and region and n-type and p-type and floating and gate and concentration and (first adj conductivity) and (second adj conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 13:36
L3	1	("6420231").PN.	USPAT	OR	OFF	2005/09/23 13:36
L4	1	("6388293").PN.	USPAT	OR	OFF	2005/09/23 13:36